1.8V Drive Nch+Nch MOSFET US6K4

Structure

Silicon N-channel MOSFET

Features

- 1) Two Nch MOSFETs are put in TUMT6 package.
- 2) High-speed switching, Low On-resistance.
- 3) 1.8V drive.

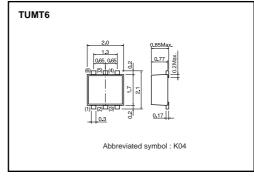
Applications

Switching

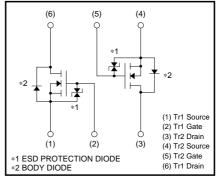
Packaging specifications

	Package	Taping		
Туре	Code	TR		
	Basic ordering unit (pieces)	3000		
US6K4	·	0		

•Dimensions (Unit : mm)



Inner circuit



•Absolute maximum ratings (Ta=25°C) <It is the same ratings for the Tr1 and Tr2>

•				
Parameter		Symbol	Limits	Unit
Drain-source voltage		Vdss	20	V
Gate-source voltage		Vgss	±10	V
Drain current	Continuous	ID	±1.5	A
Drain current	Pulsed	I _{DP} *1	±3.0	A
Source current (Body diode)	Continuous	ls	0.6	A
	Pulsed	Isp *1	2.4	A
Total power dissipation		P₀ *2	1.0	W / TOTAL
		I D	0.7	W / ELEMENT
Channel temperature		Tch	150	°C
Range of storage temperature		Tstg	-55 to +150	°C

∗1 Pw≤10μs, Duty cycle≤1%

*2 Mounted on a ceramic board

Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	Rth(ch-a)*	125	°C/W / TOTAL
	Run(cn-a)	179	°C/W / ELEMENT

* Mounted on a ceramic board



Transistors

●Electrical characteristics (Ta=25°C)

<lt is the same characteristics for the Tr1 and Tr2> $\,$

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions	
Gate-source leakage	Igss	-	_	±10	μΑ	V _{GS} =±10V, V _{DS} =0V	
Drain-source breakdown voltage	V(BR) DSS	20	_	_	V	I _D = 1mA, V _{GS} =0V	
Zero gate voltage drain current	IDSS	-	-	1	μΑ	V _{DS} = 20V, V _{GS} =0V	
Gate threshold voltage	VGS (th)	0.3	_	1.0	V	V _{DS} = 10V, I _D = 1mA	
		-	130	180	mΩ	ID= 1.5A, VGs= 4.5V	
Static drain-source on-state	RDS (on)*	-	170	240	mΩ	I _D = 1.5A, V _{GS} = 2.5V	
resistance		-	220	310	mΩ	I _D = 0.8A, V _{GS} = 1.8V	
Forward transfer admittance	Y _{fs} *	1.6	-	-	S	V _{DS} = 10V, I _D = 1.5A	
Input capacitance	Ciss	-	110	-	pF	VDS= 10V	
Output capacitance	Coss	-	18	-	pF	V _{GS} =0V	
Reverse transfer capacitance	Crss	-	15	-	pF	f=1MHz	
Turn-on delay time	td (on) *	-	5	-	ns	ID= 1.0A	
Rise time	tr *	_	5	_	ns	VDD≒10V	
Turn-off delay time	t _{d (off)} *	_	20	-	ns	VGs= 4.5V RL= 10Ω	
Fall time	t _f *	_	3	_	ns	$R_{GS}=10\Omega$	
Total gate charge	Qg *	-	1.8	2.5	nC	V _{DD} ≒10V	
Gate-source charge	Qgs *	_	0.3	-	nC	V _{GS} = 4.5V	
Gate-drain charge	Q _{gd} *	_	0.3	-	nC	ID= 1.5A	

*Pulsed

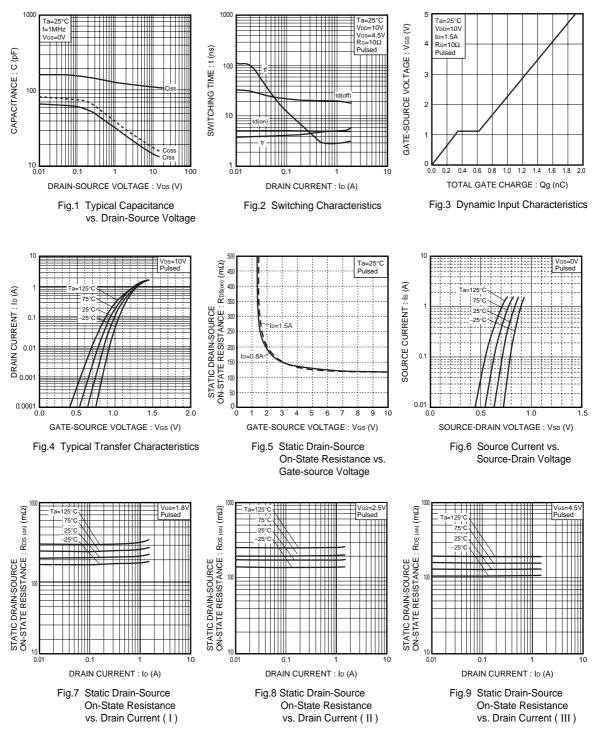
•Body diode characteristics (Source-drain) (Ta=25°C)

< It is the same characteristics for the Tr1 and Tr2>

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	Vsd	-	-	1.2	V	Is= 0.6A, V _{GS} =0V

Transistors





Notice

This product might cause chip aging and breakdown under the large electrified environment. Please consider to design ESD protection circuit.

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Appendix1-Rev2.0

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